

## Papers by Bell Laboratories Authors

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**Investigation of the Ti-Pt Diffusion Barrier for Gold Beam Lead on Aluminum.** S. P. Murarka, H. J. Levinstein, I. Blech, T. T. Sheng, and M. H. Read, *J. Electrochem. Soc.*, **125** (January 1978), pp. 156-162.

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## MATERIALS SCIENCE AND ENGINEERING

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